

2SA1505

PNP Silicon Epitaxial Planar Transistor

for switching and AF amplifier applications.

The transistor is subdivided into two groups, O and Y, according to its DC current gain.

On special request, these transistors can be manufactured in different pin configurations.



1. Emitter 2. Collector 3. Base
TO-92 Plastic Package

Absolute Maximum Ratings ($T_a = 25^\circ\text{C}$)

Parameter	Symbol	Value	Unit
Collector Base Voltage	$-V_{CBO}$	35	V
Collector Emitter Voltage	$-V_{CEO}$	30	V
Emitter Base Voltage	$-V_{EBO}$	5	V
Collector Current	$-I_C$	500	mA
Base Current	$-I_B$	50	mA
Power Dissipation	P_{tot}	150	mW
Junction Temperature	T_j	150	$^\circ\text{C}$
Storage Temperature Range	T_{stg}	- 55 to + 150	$^\circ\text{C}$

Characteristics at $T_a = 25^\circ\text{C}$

Parameter	Symbol	Min.	Typ.	Max.	Unit
DC Current Gain at $-V_{CE} = 1\text{ V}$, $-I_C = 100\text{ mA}$ at $-V_{CE} = 6\text{ V}$, $-I_C = 400\text{ mA}$ Current Gain Group	O	h_{FE}	70	-	-
	Y	h_{FE}	120	-	-
	O	h_{FE}	25	-	-
	Y	h_{FE}	40	-	-
Collector Base Cutoff Current at $-V_{CB} = 35\text{ V}$	$-I_{CBO}$	-	-	0.1	μA
Emitter Base Cutoff Current at $-V_{EB} = 5\text{ V}$	$-I_{EBO}$	-	-	0.1	μA
Collector Emitter Saturation Voltage at $-I_C = 100\text{ mA}$, $-I_B = 10\text{ mA}$	$-V_{CE(sat)}$	-	0.1	0.25	V
Base Emitter Voltage at $-V_{CE} = 1\text{ V}$, $-I_C = 100\text{ mA}$	$-V_{BE}$	-	0.8	1	V
Gain Bandwidth Product at $-V_{CE} = 6\text{ V}$, $-I_C = 20\text{ mA}$	f_T	-	200	-	MHz
Output Capacitance at $-V_{CB} = 6\text{ V}$, $f = 1\text{ MHz}$	C_{ob}	-	13	-	pF

